









PROGRAM

AM-FPD 22

THE TWENTY-NINTH INTERNATIONAL WORKSHOP ON

ACTIVE-MATRIX FLATPANEL DISPLAYS AND DEVICES

-TFT TECHNOLOGIES AND FPD MATERIALS-

July 5 - 8, 2022 Ryukoku University Avanti Kyoto Hall Kyoto, Japan This workshop is held in hybrid format with Zoom.

Sponsorship:

International Society of Functional Thin Film Materials & Devices

Technical Sponsorship:

The Electrochemical Society - Electronics and Photonics Division - The Electrochemical Society - Japan Section - IEEE Electron Devices Society

In cooperation with:

The Japan Society of Applied Physics

The Institute of Electronics, Information and Communication Engineers

The Institute of Image Information and Television Engineers

The Institute of Electrical Engineers of Japan

The Chemical Society of Japan

The Laser Society of Japan

Japanese Liquid Crystal Society

Thin Film Materials & Devices Meeting

Society of Automotive Engineers of Japan, Inc.

Society for Information Display

GENERAL INFORMATION

The 29th International Workshop on Active-Matrix Flatpanel Displays and Devices (AM-FPD '22) will be held as an online meeting from July 5 (Tuesday) to 8 (Friday), 2022. This international workshop was established in 1994 to present the latest research and development in Active-Matrix Liquid Crystal Display technologies and their applications. In addition to AMLCDs and AMOLEDs, the scope has been widened to novel flat panel displays, materials for displays, flexible technologies, related physical phenomena and novel thin-film devices such as thin-film transistors (TFT), photovoltaics (PV) technologies, and other thin-film materials and devices (TFMD).

We hope that you will attend and enjoy our workshop.

WORKSHOP THEME

AM-FPD '22 will prepare an attractive program focusing on "Prepare for Evolutional Progress after the Pandemic!".

SYMPOSIA

In addition to the regular sessions, we will prepare symposia which numerous speakers discuss for attractive and interesting themes.

Special Symposium on Vehicular Displays will focus on exciting developments paving the future of invehicle displays. The automotive industry is currently experiencing profound changes in its business environment, which will also have a strong impact on design and requirements of the human-vehicular interface, specifically displays.

Symposia, "Micro-LED Technologies", "Recent Advances in TFT Technologies for Future Electronics", "Halide Perovskite Solar Cells: Towards a Higher Horizon of Evolution" and "Development of Emerging and Neuromorphic Devices" are scheduled. Invited speakers will talk about the latest topics from the viewpoints of functional materials, device structures, fabrication processes, driving schemes, circuit technologies, etc.

PRESENTATION TIMES FOR SPEAKERS

	Total	Presentation	Discussion
Keynote	45 min.	40 min.	5 min.
Special Symposium	40 min.	35 min.	5 min.
Invited	25 min.	20 min.	5 min.
Symposium	30 min.	25 min.	5 min.
Oral	20 min.	15 min.	5 min.
Late News	15 min.	12 min.	3 min.
Poster	15:30-17:00, July 7		

THE PROCEEDINGS OF AM-FPD '22

The Proceedings of AM-FPD '22 will be distributed in our workshop special website from July 5.

LANGUAGE

The official language of the workshop is English.

REGISTRATION

For Registration, access our online registration page (http://www.amfpd.jp) and enroll your information and complete payment. Registration fee is discounted until June 10 (JST). Registration and other fees should be paid in Japanese yen via credit cards. VISA, Master, AMEX are acceptable. Apple Pay and Google Play are also acceptable. The receipt can be downloaded after your payment has been completed.

Category	Advance Registration Fee until June 10, 2022 (JST)	Registration Fee	[One day] Special Symposium	
WORKSHOP*1			Only*2	
Member* ³	¥50,000	¥55,000	1	
Non-Member	¥52,000	¥57,000		
Student	¥20,000	¥22,000		
Senior*4	¥25,000			
TUTORIAL				
Regular	Tutorial Only	¥7,000		
	Conference Attendee	¥5,000		
Student		Free		

^{*1}The registration fee of the workshop includes the admission to all sessions and the proceedings.

ON-DEMAND VIEWING

The video recordings of oral presentation will be available to watch online from July 19 (Tue.) to August 18(Thu.)

CANCELLATION POLICY

In case of cancellation after payment, please contact to the secretariat (secretariat@amfpd.jp). Cancel Charge

Before June 10-----Cancel fee 5%

After June 11-----100% of the registration fee / NO REFUND

The Proceedings of the AM-FPD '22 (download password) and on-demand viewing will be available.

^{*2}One day pass of "Special Symposium Only" is available to attend Special Symposium on Wednesday, July 6. The proceedings of the AMFPD '22 is included in the fee.

^{*3}The member of the societies which sponsor and support AM-FPD '22.

^{*4}The category of senior is for attendees who are 65 years old or older

Endorsement Letter

The endorsement letters to IEEE Journal Electron Device Society (J-EDS) or ECS Journal Solid State Science and Technology (JSS) will be issued for excellent papers, which are chosen at our internal rating processes by AMFPD program committees.

Please select which journal you wish getting the endorsement letter when you submit a paper to AM-FPD.

- 1. Endorsement letters will be issued to excellent papers from the AM-FPD committee after AM-FPD '22 workshop is held.
- 2. After you receive the endorsement letter,
 - Please attach your paper of AM-FPD '22 and the endorsement letter when submitting your manuscript to each journal,
 - You make sure to add in your reference list when you reuse the contents (figures / tables) used in your paper of AM-FPD '22.

Your ID and password are required to be registered before submitting your manuscript to each journal.

IEEE XPLORE DIGITAL LIBRARY

The Proceedings of AM-FPD '22 will be published in the IEEE Xplore digital library in around 2 months after the workshop.

TUTORIAL

These classes are widely aimed at many people from beginners to researchers who hope to review their knowledge. Presentations and documents will be in Japanese. Documents will be distributed to the participants who have registered in advance. These classes are available for an additional fee (see page 2).

Tuesday, July 5 (9 : 30 \sim 11 : 30)

- 9:30 (T-1) Working Principle and Evaluation Methods of Crystalline Silicon Solar Cells Keisuke Ohdaira, *JAIST*, *Japan*
- 10:30 (T-2) History and the Subjects of LTPS Technology for the Future (A Message to Young Scientists)

 Takashi Noguchi, *Univ. of the Ryukyus, Japan*

AWARDS

Papers presented at this workshop will be considered for "AM-FPD Paper Awards", "AMFPD-ECS Japan Section Young Researcher Award". These winners will be presented at the award ceremony in AM-FPD '23 workshop.

AM-FPD Paper Awards

"Best Paper Award", "Poster Award" and "Student Paper Award" will be presented. The winners of them are selected by AMFPD '22 award committee chaired by Professor Yukiharu Uraoka (*NAIST*).

AMFPD-ECS Japan Section Young Researcher Award

ECS Japan Section and AM-FPD Organizing Committee have jointly established "AMFPD-ECS Japan Section Young Researcher Award". This award will be given to the author under the age of 35 that belongs to the university or the research institute in Japan.

AM-FPD '21 PAPER AWARD

Best Paper Award

(2_3) Peeling Technique by Two-Dimensional MoSe₂ Atomic Layer for Bifacial-Flexible Cu (In,Ga) Se₂ Solar Cells

Takahito Nishimura, Abdurashid Mavlonov, Jakapan Chantana *Ritsumeikan Univ., Japan*

Poster Paper Award

(P 02) Characteristics of argon-ion-implanted amorphous-InGaZnO

Keisuke Yasuta¹, Toshimasa Ui¹, Takuya Ikeda², Daisuke Matsuo², Toshihiko Sakai², Shojiro Dohi¹, Yoshitaka Setoguchi², Eiji Takahashi², Yasunori Andoh², Junichi Tatemichi ¹Nisshin Ion Equipment Co., Ltd., Japan, ²Nisshin Electric Co., Ltd., Japan

Student Paper Award

Htet Su Wai, Kochi Univ. of Technol., Japan

(4_3) Oxygen Ratio Effect on Zinc Oxide Films Fabricated by Radio Frequency Magnetron Sputterin for Photoluminescence Type Gas Sensor Application

AMFPD-ECS Japan Section Young Researcher Award

Juan Paolo Bermundo, Nara Inst. of Sci. and Technol., Japan

(5_2) High-k Solution Processed Hybrid Gate Insulators for Amorphous Oxide Thin-Film Transisters and its Temperature and Thickness Dependence

ORGANIZING COMMITTEE

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Advisor: Makoto Ohkura

Akira Okada

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Yung-Hui Yeh (ITRI)

PROGRAM

Date: Tuesday, July 5

Opening Session $(12:30\sim12:45)$

Keynote Address (12:45~15:00)

12:45-13:30 K 1 Organic and Inorganic Materials R&D for High Voltage Perovskite Photovoltaic Devices (INVITED)

T. Miyasaka^{1,*)}

1) Toin University of Yokohama, JAPAN

13:30-14:15 K 2 Molecular Engineering of Organic Photovoltaics (INVITED)

H. Imahori^{1,*)}

¹⁾ Kyoto University, JAPAN

14:15-15:00 K 3 TFT Interfaces for High Sensory Resolution at Ultralow Power (INVITED)

A. Nathan^{1,2*}), J. Yu²), C. Jiang³) and H. Ma⁴)

1) University of Cambridge, UK ²⁾ Shandong University, CHINA ³⁾ Tsinghua University, CHINA ⁴⁾ Chinese Academy of Science, CHINA

— Coffee Break —

Symposium 1: Halide Perovskite Solar Cells:

Towards a Higher Horizon of Evolution (15:20~17:20)

15:20-15:50 S1 1 Highly Stable Carbon-Based Multi-Porous-Layered-Electrode Perovskite Solar Cells (INVITED)

S. Ito^{1,*}, Y. Sakai¹, R. Tsuji¹, T. Shioki¹ and K. Ohishi¹

1) University of Hyogo, JAPAN

S1 2 Materials to Improve the Performance of Sn-Based Perovskite Solar Cells 15:50-16:20 A Wakamiya^{1,*)}, S Hu¹⁾, T Nakamura¹⁾, T Handa¹⁾, T Yamada¹⁾, M Truong¹⁾, R Murdey¹⁾, Y Kanemitsu¹⁾

¹⁾ Kyoto University, JAPAN

S1 3 Characteristics of Halide Perovskites via Low-pressure Vapor-assisted Solution Process 16:20-16:50 (LP-VASP) (INVITED)

H. Yeh¹⁾, Y. Chen¹⁾, W. Hung¹⁾, M. Li¹⁾ and P. Chen^{1,*)}

1) National Cheng Kung University, TAIWAN

16:50-17:20 S1 4 Photo-Induced Charge Carrier Dynamics of Metal Halide Perovskite (INVITED) Y. Tachibana^{1,*)}

1) RMIT University, AUSTRALIA

Symposium 2 : Micro-LED Technologies (17:20~19:00)

17:20-17:50 S2 1 Micro LED sensor eye-tracking for augmented reality glasses with embedded micro display (INVITED)

C. Luo¹), K. Liang¹), C. Chu¹), C. Lin^{1,2}), C. Chao¹), W. Kuo¹) and Y. Fang^{1,*})

¹⁾ Industrial Technology Research Institute (ITRI), TAIWAN ²⁾ National Taiwan University, TAIWAN

17:50-18:20 S2_2 Eu-doped GaN red LEDs for micro-LED displays with extremely high resolution (INVITED) Y. Fujiwara^{1,*)}, S Ichikawa¹⁾, D. Timmerman¹⁾, and J. Tatebayashi¹⁾

1) Osaka University, JAPAN

S2 3 Cylindrical Aerial LED Display 18:20-18:40

R. Hattori^{1,*})

¹⁾ Kyushu University, JAPAN

18:40-19:00 S2_4 A Novel Mini-LED Backlit Driving Circuit Using PWM Mechanism with V_{TH} and V_{SS} I-**R** Rise Compensation

C. Ke^{1,*}), Y. Lin²) and C. Lin¹)

1) National Cheng Kung University, TAIWAN

Date: Wednesday, July 6

Greeting (9:15~9:25)

Special Symposium 1: Variety of automotive technology and automotive for future (9:25~11:25)

- 09:25-10:05 SS1_1 Liquid crystal beam steering angle expander for LiDAR applications (INVITED) Y. Li^{1,*}, Z. Luo¹⁾ and S. Wu¹⁾

 1) University of Central Florida, U.S.A.
- 10:05-10:45 SS1_2 High Performance Active-Matrix Light-Emitting Displays Enabled by Vertical Light-Emitting Transistor Technology (INVITED)

 X. Chen¹, H. Katsui², K. Miyachi², W. Youn¹, I.S. Cho¹, C. Samouce¹, D. Cheney¹, R. Jayaraman¹, A. Titov¹, R. Das¹, A. Schachtner¹, J. Alvarez³, S. Vasilyeva¹, A. Rinzler^{1,3}, M. Lemaitre¹ and B. Liu^{1,*})

 1) Mattrix Technologies, USA 2) JSR Corporation, JAPAN 3) University of Florida, USA
- 10:45-11:25 SS1_3 Pixels on The Road Where Are They Headed? (INVITED)

 D.S. Hermann^{1,*})

 1) Volvo Cars, SWEDEN

— Coffee Break —

Special Symposium 2 : Market overview (11:45~12:25)

11:45-12:25 SS2_1 Automotive Display Market Outlook (Subjected to Be Changed) (INVITED) S. $Wu^{1,*}$ (Invited of the Changed) (INVITED) S. $Wu^{1,*}$ (Invited of the Changed) (INVITED)

— Lunch —

Special Symposium 3: High performance automotive displays and manufactures (13:55~15:15)

13:55-14:35 SS3_1 High-Performance Interactive Display Technologies for Automotive Applications (INVITED)
Y. Ito^{1,*}) and H. Ikeno¹⁾

Y. Ito^{1, 1)} and H. Ikeno¹⁾

Tianma Japan. JAPAN

14:35-15:15 SS3_2 Manufacturing Equipment Technology for Automotive Display (INVITED)

T. Kikuchi^{1,*})

1) ULVAC, Inc.

Special Symposium 4: Free-form, bendable automotive display and unit of mobility and innovation systems (15:35~16:55)

15:35-16:15 SS4_1 OLCD in Automotive Applications – Enabling Curved and Non-Rectangular Form Factors with Conformable Displays (INVITED)

J. Huggins^{1,*)}, M. Wheeler¹⁾, A. Russell¹⁾ and A. James¹⁾

1) FlexEnable, UK

16:15-16:55 SS4_2 Creating the Mobility and Technology Experience – Trip specific assessment of automotive display applications (INVITED)

Dipl.-Wi.-Ing. Sebastian Stegmüller^{1,*)}

1) Fraunhofer Institute for Industrial Engineering IAO, GERMANY

Closing (16:55~17:05)

Date: Thursday, July 7

Session 1 : Emerging Science, Materials, and Engineering

in Solar Cells (9:15∼10:25)

09:15-09:40 1_1 Crystal Chemistry of Organo-Lead Halide Perovskite Solar Cells S. Uchida^{1,*)}

1) University of Tokyo, JAPAN

09:40-10:05 1_2 Advanced Technologies for Ultra-Flexible and Highly Stable Organic Solar Cells (INVITED)

K. Fukuda^{1,*)} and T. Someya^{1,2)}

1) RIKEN, JAPAN 2) The University of Tokyo, JAPAN

10:05-10:25 1_3 Stabilizing Perovskite Crystals by Fixing The Position of Potassium Ion

C. Zhang¹⁾ and H. Okada^{1,*)}

1) University of Toyama, JAPAN

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— Coffee Break —

Symposium 3: Recent Advances in TFT Technologies

for Future Electronics (10:45~12:15)

10:45-11:15 S3_1 Recent Progress of Oxide TFT Based Inverter Technology (INVITED) K. Nomura^{1,*)}

1) University of California San Diego, USA

11:15-11:45 S3_2 Ferroelectric Thin-Film Transistors for Memory and Neuromorphic Device Applications (INVITED)

J. Lee^{1,*})

1) POSTECH, KOREA

11:45-12:15 S3_3 T-Shaped Poly-Si Thin-Fim Transistor Technology for Advanced Logic and RF Applications (INVITED)

H. Lin^{1,*}), C. Lee¹), P. Yu¹), P. Li¹), K. Chen²) and G. Huang²)

¹⁾ National Yang Ming Chiao Tung University, TAIWAN ²⁾ Taiwan Semiconductor Research Institute (TSRI), TAIWAN

— Lunch —

Symposium 4: Development of Emerging

and Neuromorphic Devices (13:45~15:15)

13:45-14:15 S4_1 Development of Neuromorphic Systems and Emerging Devices : Revolutionize Artificial Intelligence with Your Devices !! (INVITED)

M. Kimura^{1,2,*)}

¹⁾ Ryukoku University, JAPAN ²⁾ Nara Institute of Science and Technology, JAPAN

14:15-14:45 S4_2 Construction of a neural network using organic materials and ions (INVITED)

N. Hagiwara²⁾, S. Kan²⁾, T. Asai²⁾ and M. Akai-kasaya^{1,2,*)}

Osaka University, JAPAN Delta University, JAPAN

14:45-15:15 S4_3 In-Materio Computing Devices Composed of Random Network Nanoparticles for Future Autonomous Robot Operation (INVITED)

H. Tanaka^{1,*)}

1) Kyushu Institute of Technology, JAPAN

Poster Session (15:30∼17:00)

P_1 Novel AMOLED Compensation Pixel Circuit Design with Low Frame Rate for Portable Displays C. Fan^{1,2)}, W. Lin^{1,*)} and C. Chen¹⁾

1) National Taiwan University of Science and Technology, TAIWAN

P_2 New Compensating Pixel Circuit to Mitigate Impact of Leakage Currents on OLED Currents for AMOLED Displays

W. Shieh^{1,*}, C. Tsai¹⁾, B. Chen¹⁾ and C. Lin¹⁾

1) National Cheng Kung University, TAIWAN

P_3 Dependence of Conversion Properties in GTO Thin Film Thermoelectric Devices on Hydrochloric Acid Concentration in Mist CVD Method

R. Ito^{1,*)}, S. Sugisaki¹⁾, Y. Yamamoto¹⁾, N. Shibata¹⁾ and M. Kimura¹⁾

1) Ryukoku University, JAPAN

P_4 Spike-Timing-Dependent-Plasticity Characterization of Ga-Sn-O Thin Film Synaptic Device

K. Yachida^{1,*)}, T. Katagiri¹⁾, N. Komai¹⁾, N. Sahara¹⁾ and M. Kimura^{1,2)}

¹⁾ Ryukoku University, JAPAN ²⁾ Nara Institute of Science and Technology, JAPAN

P_5 Research on structural stabilization method of GeO2 film and improvement of electrical characteristics H. Iino^{1,*}), T. Shibuya¹⁾, Y. Iwazaki¹⁾ and T. Ueno¹⁾

1) Tokyo University of Agriculture and Technology, JAPAN

P 6 Study on Fabrication of GeO₂/Ge Structure with Good Interfacial Properties

K. Ito¹⁾, K. Matsuura^{1,*)}, H. Takahashi¹⁾, H. Saito¹⁾, Y. Iwazaki¹⁾ and T. Ueno¹⁾

1) Tokyo University of Agriculture and Technology, JAPAN

P_7 Solid-Phase Crystallization Characteristics of Interface-Modulated Sn-Doped Ge Thin Films on Insulator with Capping

T. Nagano^{1,*}), R. Hara¹⁾ and T. Sadoh¹⁾

1) Kyushu University, JAPAN

P_8 Interplay of Viscosities in Controlling The Orientation of Conjugated Polymer Thin Films Fabricated by Floating Film Transfer Method

S. Sharma^{1,*)}, A.K. Vats²⁾, S. Nagamatsu¹⁾ and S.S. Pandey¹⁾

¹⁾ Kyushu Institute of Technology, JAPAN ²⁾ Nara Advanced Institute of Science and Technology, JAPAN

P 9 GTO thin film thermoelectric conversion device annealed in vacuum and in air

Y. Yamamoto^{1,*)}, R. Ito¹⁾, N. Shibata¹⁾ and M. Kimura¹⁾

1) Ryukoku University, JAPAN

P_10 Fabrication and Characterization of Oriented Thin Films of DPP-Based Conjugated Copolymer Prepared by Friction Transfer Method

Y. Kurokawa^{1,2,*)}, A.K. Vats²⁾, S. Nagamatsu³⁾ and S.S. Pandey¹⁾

¹⁾ Graduate School of Life Science and Systems Engineering, JAPAN ²⁾ Nara Institute of Science and Technology, JAPAN ³⁾ Kyushu Institute of Technology, JAPAN

P 11 Fabrication of ZnO Nanorods and Applied for Flexible Dye-Sensitized Solar Cells

H.S. Wai^{1,*)}, M. Morimoto¹⁾ and C. Li¹⁾

1) Kochi University of Technology, JAPAN

P_12 Photoinduced Phase Transition and Subsequent Change in Adhesion Property of Cyanostilbene Liquid Crystalline Polymer Composite

M. Kondo^{1*)}, S. So¹⁾, T. Nagata¹⁾, H. Adachi¹⁾, D. Okai¹⁾ and N. Kawatsuki¹⁾

1) University of Hyogo, JAPAN

P_13 Photon Flux Density Dependence of Nanographene Synthesis by Soft X-Ray Irradiation From Pentacene-Based Molecules Prepared on Ni Films by Hot Mesh Deposition

A. Heya^{1,*}, K. Kanda¹, R. Yamasaki² and K. Sumitomo¹

1) University of Hyogo, JAPAN 2) Tocalo Co., Ltd., JAPAN

P L1 Fixed Charge Induced by Ion Implantation Used to Control The Threshold Voltage for Oxide TFTs

T. Sakai^{1,*}), D. Matsuo¹⁾, M. Fujiwara¹⁾, D. Azuma¹⁾, Y. Setoguchi¹⁾, Y. Andoh¹⁾, E. Takahashi¹⁾ and

T. Sameshima²⁾

1) NISSIN ELECTRIC CO., JAPAN 2) Tokyo University of Agriculture and Technology, JAPAN

P L2 Performance of N- and P-Ch Self-Aligned Planar Double-Gate Cu-MIC Poly-Ge TFTs on Glass Substrates

S. Suzuki^{1,*)}, K. Tomizuka¹⁾ and A. Hara¹⁾

Tohoku Gakuin University, JAPAN

P L3 Four-Terminal Poly-Si Thin-Film Transistors with High-K Gate Dielectric on Glass Substrate and Its **Application in CMOS Inverters**

K. Nomura^{1,*)}, A. Nagayosi¹⁾ and A. Hara¹⁾

1) Tohoku Gakuin University, JAPAN

P L4 In-Ga-Zn-O TFT Using Hf_{0.5}Zn_{0.5}O₂ Deposited by RF Magnetron Sputtering As The Gate Insulating

T. Fukui^{1,*)}, K. Nakagawa¹⁾, R. Edahiro¹⁾, H. Kawanishi¹⁾ and M. Kimura¹⁾

1) Rvukoku University, JAPAN

P L5 Influence of Sn Concentration on The Performance of Solution Combustion Synthesis-Assisted Si_XSn_YO Thin-Film Transistors

C.G.P. Quino^{1,*)}, J.P. Bermundo¹⁾, M. Uenuma¹⁾ and Y. Uraoka¹⁾

1) Nara Institute of Science and Technology, JAPAN

P L6 Investigation of Infrared Absorption Properties of InGaZnO Thin Film in TFT Using Monochromated **STEM-EELS**

N. Kawasaki^{1,*)}, S. Inamoto¹⁾ and Y. Otsuka¹⁾

1) Toray Research Center Inc., JAPAN

P L7 Fabrication and Characteristics of Weak Microcavity AC-Driven Insulated Polymer

Electroluminescent Devices with Dielectric Film Mirrors Utilizing Ferroelectric Polymer Poly(Vinylidene Fluoride-Trifluoroethylene) Film

H.Kajii^{1,*)}, Y. Takayama¹⁾, M. Morifuji¹⁾ and M. Kondow¹⁾

1) Osaka University, JAPAN

P L8 Synaptic Characteristics of Ferroelectric Capacitors for Neuromorphic Systems

Y. Ishisaki^{1,*}, O. Tanaka¹, T. Kuwahara¹, H. Kawanishi¹ and M. Kimura¹

1) Ryukoku University, JAPAN

P L9 ReRAM Multi-Level Characteristics for Analog Computing

T. Katagiri^{1,*}, K. Morigaki¹, K. Yachida¹, H. Kawanishi¹ and M. Kimura¹

1) Ryukoku University, JAPAN

Date: Friday, July 8

Session 2 : Recent Progress in Flat Panel Display 1 (9:15~10:20)

09:15-09:40 2_1 FOD Solution with High-PPI Flexible Image Sensor under OLED Panel (INVITED)

F. Lu^{1,*}, H. Yu¹, K. Li¹, W. Guo¹, Q. Yao¹, Y. Zeng¹, Y. Wu¹ and Y. Ding¹

Shanghai Tianma Microelectronics Co., CHINA

09:40-10:00 2_2 Stretchable AMOLED Display Pixel Circuit Compensating for V_{Th} Variation and Strain Effect

J. Kang^{1,*)}, K. Kang¹⁾, J. Park¹⁾, M. Kong¹⁾ and S. Lee¹⁾

1) Seoul National University, KOREA

10:00-10:20 2_3 Crosstalk and Uniformity Analysis of Fingerprint-On-Display Technology Using Pinhole Imaging Technique

M.A.B. Misran^{1,*} and R. Hattori¹⁾

Nyushu University, JAPAN.

— Coffee Break —

Session 3: Intelligent devices and systems

Chairpersons: A. Heya, *University of Hyogo, JAPAN*H. Kajii, *Osaka University, JAPAN*Shyam S. Pandy, *Kyushu Institute of Technology, JAPAN*

10:40-11:05 3_1 Phase Diagram Construction Supported by Artificial Intelligence (INVITED) R. Tamura^{1,*})

¹⁾ International Center for Materials Nanoarchitectonics(MANA), National Institute for Materials Science, JAPAN

11:05-11:25 3_2 Character Inference Learning for Stacked Neuromorphic Devices Using IGZO Thin Films

E.Iwagi^{1,*)}, M. Kimura^{1,2)}

1) Ryukoku University, JAPAN 2) Nara Institute of Science and Technology, JAPAN

11:25-11:45 3_3 Structural Modification of Solution-Processed Barium Titanate/Polysiloxane Nanocomposite for Memory Application

A.S. Safaruddin^{1,*)}, J.P.S. Bermundo¹⁾, M. Uenuma¹⁾, A. Yamamoto²⁾, M. Kimura³⁾ and Y. Uraoka

¹⁾ Nara Institute of Science and Technology, JAPAN ²⁾ Merck Electronics, JAPAN ³⁾ Ryukoku

University, JAPAN

— Lunch —

Session 4:Recent Progress in Flat Panel Display 2 (13:15~14:15)

13:15-13:35 4 1 Material Networks for Neuromorphic Computing

T. Matsumoto^{1,*)}

1) Osaka University, JAPAN

13:35-13:55 4_2 High-Performance Bio-Memristive Devices with Natural Egg Albumen as a Switching Layer

S. Chattaraj¹⁾, A. Dwivedi¹⁾, G. Konwar¹⁾, A. Lodhi¹⁾, S. Saini¹⁾ and S.P. Tiwari^{1,*)}

1) Indian Institute of Technology Jodhpur, INDIA

13:55-14:15 4_3 Fabrication of ZnCuInS/ZnS Based Quantum-Dot Light-Emitting Diodes with Variation of Hole Transport Materials in Mixed Single Layer

M.M.R. Biswas^{1,*)} and H. Okada¹⁾

1) University of Toyama, JAPAN

Session 5: Advanced Process and Materials for TFT and Display Technologies (14:35~15:40)

14:35-15:00 5_1 Solid Phase Crystallization of Hydrogenated Indium Oxide (InO_X:H) for High Mobility Thin-Film Transistors (INVITED)

M. Furuta^{1,*)}, T. Kataoka¹⁾, Y. Magari²⁾ and W. Yeh²⁾

¹⁾ Kochi University of Technology, JAPAN ²⁾ Shimane University, JAPAN

15:00-15:20 5_2 High Performance Flexible Organic Transistors with Biodegradable Natural-Protein Based Gate Dielectrics

G. Konwar, ^{1,*}), P. Saxena¹⁾, V. Raghuwanshi¹⁾, S. Rahi¹⁾ and S.P. Tiwari¹⁾

1) Indian Institute of Technology Jodhpur, INDIA

15:20-15:40 5_3 Comparative Study of Cu Film Properties on CuMn and Mo Adhesion Layers Use as Bottom Electrodes in Display Devices

H. Kim^{1,*}, B. Zhu¹, M. Huang¹, R. Vaddi¹ and R.G. Manley¹

1) Corning Research and Development Corporation, USA

LATE NEWS

15:40-15:55 L_1 Direct Patterning Process Development for Solution Based Electrodes of TFTs

S. Tanaka^{1,*}), M. Miyakawa¹⁾, H. Tsuji¹⁾, T. Takei¹⁾ and M. Nakata¹⁾

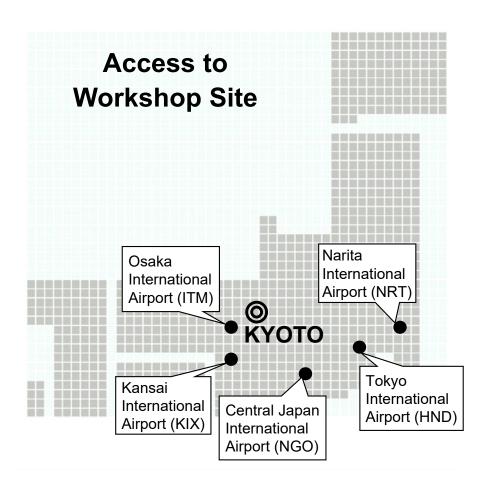
1) NHK Science & Technology Research Laboratories, JAPAN

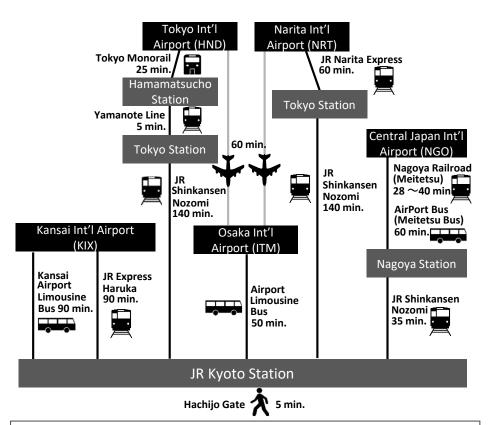
15:55-16:10 L_2 Electrical Performance Improvement of All-Solution Processed Indium Zinc Oxide Thin-Film Transistor by UV-Irradiation Treatment

U. Hanifah^{1,*)}, J.P.S. Bermundo¹⁾, M. Uenuma¹⁾ and Y. Uraoka¹⁾

1) Nara Institute of Science and Technology, JAPAN

Closing Remarks (16:10~16:15)





Ryukoku University Avanti Kyoto Hall (Avanti 9th Floor) 龍谷大学響都ホール校友会館



THE TWENTY-NINTH INTERNATIONAL WORKSHOP ON ACTIVE-MATRIX FLATPANEL DISPLAYS AND DEVICES —TFT TECHNOLOGIES AND FPD MATERIALS — (AM-FPD '22)

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